

LT1190

FEATURES

- Gain Bandwidth Product, A_V = 1: 50MHz
- Slew Rate: 450V/µs
- Low Cost
- Output Current: ±50mA
- Settling Time: 140ns to 0.1%
- Differential Gain Error: 0.1%, (R_L = 1k)
- Differential Phase Error: 0.06° , $(R_1 = 1k)$
- High Open-Loop Gain: 10V/mV Min
- Single Supply 5V Operation
- Output Shutdown

APPLICATIONS

- Video Cable Drivers
- Video Signal Processing
- Fast Integrators
- Pulse Amplifiers
- D/A Current to Voltage Conversion

TYPICAL APPLICATION



Ultrahigh Speed Operational Amplifier

DESCRIPTION

The LT[®]1190 is a video operational amplifier optimized for operation on \pm 5V, and a single 5V supply. Unlike many high speed amplifiers, this amplifier features high open-loop gain, over 85dB, and the ability to drive heavy loads to a full-power bandwidth of 20MHz at 7V_{P-P}. In addition to its very fast slew rate, the LT1190 features a unity-gain-stable bandwidth of 50MHz and a 75° phase margin, making it extremely easy to use.

Because the LT1190 is a true operational amplifier, it is an ideal choice for wideband signal conditioning, fast integrators, active filters, and applications requiring speed, accuracy and low cost.

The LT1190 is available in 8-pin PDIP and SO packages with standard pinouts. The normally unused Pin 5 is used for a shutdown feature that shuts off the output and reduces power dissipation to a mere 15mW.

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TECHNOLOGY

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ABSOLUTE MAXIMUM RATINGS

(Note 1)	
Total Supply Voltage (V + to V -)	18V
Differential Input Voltage	±6V
Input Voltage	±V _S
Output Short-Circuit Duration (Note 2).	Continuous
Maximum Junction Temperature	150°C
Operating Temperature Range	
TTTTOOM (ODCOLETE)	EE00 to 1000

	-55 0 10 125 0
LT1190C	0°C to 70°C
Storage Temperature Range	–65°C to 150°C
Lead Temperature (Soldering, 10 sec)	300°C

PACKAGE/ORDER INFORMATION



Consult LTC Marketing for parts specified with wider operating temperature ranges.

$\label{eq:characteristics} \textbf{V}_{S} = \pm 5 \textbf{V}, \ \textbf{T}_{A} = 25^{\circ} \textbf{C}, \ \textbf{C}_{L} \leq 10 p F, \ Pin \ 5 \ open \ circuit \ unless \ otherwise \ noted.$

CVMDOI	DADAMETED		CONDITIONS	MIN	LT1190M/		
SYMBOL	PARAMETER		CONDITIONS	MIN	ТҮР	MAX	UNITS
V _{OS}	Input Offset Voltage	е	N8 Package		3	10	mV
			SO-8 Package			15	mV
l _{OS}	Input Offset Curren	t			0.2	1.7	μΑ
Ι _Β	Input Bias Current				±0.5	±2.5	μΑ
en	Input Noise Voltage	9	$f_0 = 10 kHz$		50		nV/√Hz
i _n	Input Noise Curren	t	f ₀ = 10kHz		4		pA/√Hz
R _{IN}	Input Resistance	Differential Mode			130		kΩ
		Common Mode			5		MΩ
CIN	Input Capacitance		A _V = 1		2.2		pF
	Input Voltage Rang	e	(Note 3)	-2.5		3.5	V
CMRR	Common Mode Re	jection Ratio	$V_{CM} = -2.5V$ to 3.5V	60	70		dB
PSRR	Power Supply Reje	ction Ratio	$V_{S} = \pm 2.375V \text{ to } \pm 8V$	60	70		dB
A _{VOL}	Large-Signal Voltag	ge Gain	$R_{L} = 1k, V_{0} = \pm 3V$	10	22		V/mV
			$R_L = 100\Omega, V_0 = \pm 3V$	2.5	6		V/mV
			$V_{\rm S} = \pm 8 V, R_{\rm L} = 100 \Omega, V_{\rm O} = \pm 5 V$	3.5	12		V/mV
V _{OUT}	Output Voltage Swi	ing	$V_{S} = \pm 5V, R_{L} = 1k$	±3.7	± 4		V
			$V_{\rm S} = \pm 8V, R_{\rm L} = 1k$	±6.7	±7		V
SR	Slew Rate		$A_V = -1, R_L = 1k$ (Notes 4, 9)	325	450		V/µs
FPBW	Full-Power Bandwi	dth	$V_0 = 6V_{P-P}$ (Note 5)	17.2	23.9		MHz
GBW	Gain Bandwidth Pro	oduct			50		MHz
t _{r1} , t _{f1}	Rise Time, Fall Tim	е	$A_V = 50, V_0 = \pm 1.5V, 20\%$ to 80%, (Note 9)	175	250	325	ns
t _{r2} , t _{f2}	Rise Time, Fall Tim	е	$A_V = 1, V_0 = \pm 125 mV, 10\%$ to 90%		1.9		ns
t _{PD}	Propagation Delay		$A_V = 1, V_0 = \pm 125 mV, 50\%$ to 50%		2.4		ns
	Overshoot		$A_V = 1, V_0 = \pm 125 mV$		5		%
ts	Settling Time		3V Step, 0.1% (Note 6)		140		ns



$\label{eq:VS} \textbf{ELECTRICAL CHARACTERISTICS} \quad \textbf{V}_{S} = \pm 5 \textbf{V}, \ \textbf{T}_{A} = 25^{\circ} \textbf{C}, \ \textbf{C}_{L} \leq 10 pF, \ Pin \ 5 \ open \ circuit \ unless \ otherwise \ noted.$

				LT1190M/C		
SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNITS
Diff A _V	Differential Gain	$R_L = 150\Omega, A_V = 2$ (Note 7)		0.35		%
Diff Ph	Differential Phase	$R_L = 150\Omega$, $A_V = 2$ (Note 7)		0.16		Deg _{P-P}
Is	Supply Current			32	38	mA
	Shutdown Supply Current	Pin 5 at V ⁻		1.3	2	mA
I _{SHDN}	Shutdown Pin Current	Pin 5 at V ⁻		20	50	μA
t _{ON}	Turn On Time	Pin 5 from V ⁻ to Ground, $R_L = 1k$		100		ns
t _{OFF}	Turn Off Time	Pin 5 from Ground to V ⁻ , $R_L = 1k$		400		ns

$V_S{}^+$ = 5V, $V_S{}^-$ = 0V, V_{CM} = 2.5V, T_A = 25°C, $C_L \leq$ 10pF, Pin 5 open circuit unless otherwise noted.

CVMDOI		CONDITIONS			LT1190M/		
SYMBOL	PARAMETER	CONDITIONS		MIN	ТҮР	MAX	UNITS
V _{OS}	Input Offset Voltage	÷.	N8 Package		3	11	mV
		SO-8 Package				15	mV
l _{OS}	Input Offset Current				0.2	1.2	μA
I _B	Input Bias Current				±0.5	±1.5	μA
	Input Voltage Range	(Note 3)		2		3.5	V
CMRR	Common Mode Rejection Ratio	V _{CM} = 2V to 3.5V	V _{CM} = 2V to 3.5V		70		dB
A _{VOL}	Large-Signal Voltage Gain	$R_L = 100\Omega$ to Ground, $V_0 = 1V$ to $3V$		2.5	7		V/mV
V _{OUT}	Output Voltage Swing	$R_L = 100\Omega$ to Ground	V _{OUT} High	3.6	3.8		V
			V _{OUT} Low		0.25	0.4	V
SR	Slew Rate	$A_V = -1$, $V_0 = 1V$ to $3V$	·		250		V/µs
GBW	Gain Bandwidth Product				47		MHz
I _S	Supply Current			24.5	29	36	mA
	Shutdown Supply Current	Pin 5 at V ⁻			1.2	2	mA
I _{SHDN}	Shutdown Pin Current	Pin 5 at V ⁻			20	50	μA

The \bullet denotes the specifications which apply over the full operating temperature range of $-55^{\circ}C \le T_A \le 125^{\circ}C$. $V_S = \pm 5V$, Pin 5 open circuit unless otherwise noted.

					LT1190M		
SYMBOL	PARAMETER	CONDITIONS		MIN	ТҮР	MAX	UNITS
V _{OS}	Input Offset Voltage	N8 Package	•		5	14	mV
$\Delta V_{0S} / \Delta T$	Input V _{OS} Drift		•		16		µV/°C
I _{OS}	Input Offset Current		•		0.2	2	μA
I _B	Input Bias Current		•		±0.5	±2.5	μA
CMRR	Common Mode Rejection Ratio	V _{CM} = -2.5V to 3.5V	•	55	70		dB
PSRR	Power Supply Rejection Ratio	$V_{S} = \pm 2.375 V \text{ to } \pm 5 V$	•	55	70		dB
A _{VOL}	Large-Signal Voltage Gain	$R_L = 1k, V_0 = \pm 3V$ $R_L = 100\Omega, V_0 = \pm 3V$	•	8 1	16 2.5		V/mV V/mV
V _{OUT}	Output Voltage Swing	R _L = 1k	•	±3.7	±3.9		V
Is	Supply Current		•		32	38	mA
	Shutdown Supply Current	Pin 5 at V ⁻ (Note 8)	•		1.5	2.5	mA
I _{SHDN}	Shutdown Pin Current	Pin 5 at V $^-$	•		20		μΑ



ELECTRICAL CHARACTERISTICS The \bullet denotes the specifications which apply over the full operating temperature range of $0^{\circ}C \le T_A \le 70^{\circ}C$. $V_S = \pm 5V$, Pin 5 open circuit unless otherwise noted.

SYMBOL	PARAMETER	CONDITIONS		MIN	LT1190C Typ	MAX	UNITS
V _{OS}	Input Offset Voltage	N8 Package SO-8 Package	•		3	11 18	mV mV
$\Delta V_{0S} / \Delta T$	Input V _{OS} Drift		•		16		μV/°C
I _{OS}	Input Offset Current		•		0.2	1.7	μA
IB	Input Bias Current		•		±0.5	±2.5	μA
CMRR	Common Mode Rejection Ratio	V _{CM} = -2.5V to 3.5V	•	58	70		dB
PSRR	Power Supply Rejection Ratio	$V_{S} = \pm 2.375 V \text{ to } \pm 5 V$	•	58	70		dB
A _{VOL}	Large-Signal Voltage Gain	$R_L = 1k, V_0 = \pm 3V$ $R_L = 100\Omega, V_0 = \pm 3V$	•	9 2	20 6		V/mV V/mV
V _{OUT}	Output Voltage Swing	R _L = 1k	•	±3.7	±3.9		V
Is	Supply Current		•		32	38	mA
	Shutdown Supply Current	Pin 5 at V ⁻ (Note 8)	•		1.4	2.1	mA
I _{SHDN}	Shutdown Pin Current	Pin 5 at V $^-$	•		20		μA

Note 1: Absolute maximum ratings are those values beyond which the life of the device may be impaired.

Note 2: A heat sink is required to keep the junction temperature below absolute maximum when the output is shorted.

Note 3: Exceeding the input common mode range may cause the output to invert.

Note 4: Slew rate is measured between $\pm 1V$ on the output, with a $\pm 3V$ input step.

Note 5: Full-power bandwidth is calculated from the slew rate measurement:

FPBW = $SR/2\pi V_P$.

Note 6: Settling time measurement techniques are shown in "Take the Guesswork Out of Settling Time Measurements," EDN, September 19, 1985. $A_V = -1$, $R_L = 1k$.

Note 7: NTSC (3.58MHz). For $R_L = 1k$, Diff $A_V = 0.1\%$, Diff Ph = 0.06°. Note 8: See Applications section for shutdown at elevated temperatures. Do not operate the shutdown above $T_{J} > 125^{\circ}C$.

Note 9: AC parameters are 100% tested on the ceramic and plastic DIP packaged parts (J and N suffix) and are sample tested on every lot of the SO packaged parts (S suffix).

Optional Offset Nulling Circuit



INPUT OFFSET VOLTAGE CAN BE ADJUSTED OVER A ±150mV RANGE WITH A 1kΩ TO 10kΩ POTENTIOMETER 1 T1190 • TA03



TYPICAL PERFORMANCE CHARACTERISTICS





 $V_S = \pm 5V$

 $\begin{array}{l} V_S = \pm 5V \\ T_A = 25^\circ C \\ R_S = 100k \end{array}$

Input Bias Current

vs Temperature

vs Frequency

80

60

40

20

0

10

EQUIVALENT INPUT NOISE CURRENT (pAMHz)

-0.3

-0.4

Common Mode Voltage vs Supply Voltage



Equivalent Input Noise Voltage vs Frequency



Shutdown Supply Current vs Temperature



Open-Loop Voltage Gain

1k

FREQUENCY (Hz)

10k

100k

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100



Supply Current vs Supply Voltage



Open-Loop Voltage Gain vs Load Resistance





TYPICAL PERFORMANCE CHARACTERISTICS



LINEAR

TYPICAL PERFORMANCE CHARACTERISTICS





Small-Signal Transient Response



 $A_V = +1$, SMALL-SIGNAL RISE TIME, ^{1190 G23} WITH FET PROBES



Output Overload



 $A_V = -1, V_{IN} = 12V_{P-P}$ 1190 G24





 $A_V = +1$, $C_L = 10pF$ SCOPE PROBE ^{1190 G22}



APPLICATIONS INFORMATION

Power Supply Bypassing

The LT1190 is quite tolerant of power supply bypassing. In some applications a 0.1μ F ceramic disc capacitor placed 1/2 inch from the amplifier is all that is required. A scope photo of the amplifier output with no supply bypassing is used to demonstrate this bypassing tolerance, $R_L = 1k\Omega$.

No Supply Bypass Capacitors



 $A_V = -1$, IN DEMO BOARD, $R_L = 1k\Omega$

Supply bypassing can also affect the response in the frequency domain. It is possible to see a slight 1dB rise in the frequency response at 130MHz depending on the gain configuration, supply bypass, inductance in the supply leads and printed circuit board layout. This can be further minimized by not using a socket.

Closed-Loop Voltage Gain vs Frequency

20 $V_S = \pm 5V$ $T_A = 25^{\circ}C$ CLOSED-LOOP VOLTAGE GAIN (dB) $R_L = 1k$ 10 $A_V = 2$ $A_V = 1$ 0 -10 -20 100 1M 10M 100M 1G FREQUENCY (Hz)

LT1190 • TA05

In most applications, and those requiring good settling time, it is important to use multiple bypass capacitors. A 0.1μ F ceramic disc in parallel with a 4.7μ F tantalum is recommended. Two oscilloscope photos with different bypass conditions are used to illustrate the settling time characteristics of the amplifier. Note that although the output waveform looks acceptable at 1V/DIV, when amplified to 1mV/DIV the settling time to 2mV is 4.244μ s for the 0.1μ F bypass; the time drops to 163ns with multiple bypass capacitors.



SETTLING TIME TO 2mV, A_V = -1 SUPPLY BYPASS CAPACITORS = 0.1 μF + 4.7 μF TANTALUM



APPLICATIONS INFORMATION

Cable Terminations

The LT1190 operational amplifier has been optimized as a low cost video cable driver. The \pm 50mA guaranteed output current enables the LT1190 to easily deliver 7.5V_{P-P} into 100 Ω , while operating on \pm 5V supplies or 2.6V_{P-P} on a single 5V supply.

Double Terminated Cable Driver



Cable Driver Voltage Gain vs Frequency



When driving a cable it is important to terminate the cable to avoid unwanted reflections. This can be done in one of two ways: single termination or double termination. With single termination, the cable must be terminated at the receiving end (75Ω to ground) to absorb unwanted energy. The best performance can be obtained by double termination (75Ω in series with the output of the amplifier, and 75Ω to ground at the other end of the cable). This termination is preferred because reflected energy is absorbed at each end of the cable. When using the double termination technique it is important to note that the signal is attenuated by a factor of 2, or 6dB. This can be compensated for by taking a gain of 2, or 6dB in the amplifier. The cable driver has a – 3dB bandwidth in excess of 30MHz while driving the 150 Ω load.

Using the Shutdown Feature

The LT1190 has a unique feature that allows the amplifier to be shut down for conserving power or for multiplexing several amplifiers onto a common cable. The amplifier will shut down by taking Pin 5 to V⁻. In shutdown, the amplifier dissipates 15mW while maintaining a true high impedance output state of 15k Ω in parallel with the feedback resistors. The amplifiers must be used in a noninverting configuration for MUX applications. In inverting configurations the input signal is fed to the output through the feedback components. The following scope photos show that with very high R_L, the output is truly high impedance; the output slowly decays toward ground. Additionally, when the output is loaded with as little as 1k Ω the amplifier shuts off in 400ns. This shutoff can be under the control of HC CMOS operating between 0V and – 5V.

Output Shutdown



1MHz SINE WAVE GATED OFF WITH SHUTDOWN PIN, $A_V = 1$, $R_L = SCOPE$ PROBE



Output Shutdown

1MHz SINE WAVE GATED OFF WITH SHUTDOWN PIN, A_V = 1, R_L = 1k Ω

APPLICATIONS INFORMATION

The ability to maintain shutoff is shown on the curve Shutdown Supply Current vs Temperature in the Typical Performance Characteristics section. At very high elevated temperatures it is important to hold the shutdown pin close to the negative supply to keep the supply current from increasing.

Murphy Circuits

There are several precautions the user should take when using the LT1190 in order to realize its full capability. Although the LT1190 can drive a 50pF load, isolating the capacitance with 10Ω can be helpful. Precautions primarily have to do with driving large capacitive loads. Other precautions include:

- 1. Use a ground plane (see Design Note 50, High Frequency Amplifier Evaluation Board).
- 2. Do not use high source impedances. The input capacitance of 2pF and $R_S = 10k$ for instance, will give an 8MHz -3dB bandwidth.
- 3. PC board socket may reduce stability.
- 4. A feedback resistor of 1k or lower reduces the effects of stray capacitance at the inverting input. (For instance, closed-loop gain of 2 can use $R_{FB} = 300\Omega$ and $R_G = 300\Omega$.)



Driving Capacitive Load

 $A_V = -1$, IN DEMO BOARD, $C_L = 50$ pF



Driving Capacitive Load

 A_V = -1, IN DEMO BOARD, C_L = 50pF WITH 10 Ω ISOLATING RESISTOR

50m

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Murphy Circuits



SIMPLIFIED SCHEMATIC



^{*}SUBSTRATE DIODE, DO NOT FORWARD BIAS

PACKAGE DESCRIPTION Dimensions in inches (millimeters) unless otherwise noted.





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PACKAGE DESCRIPTION



N8 Package 8-Lead PDIP (Narrow .300 Inch)

*THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.010 INCH (0.254mm)

> S8 Package 8-Lead Plastic Small Outline (Narrow .150 Inch) (Reference LTC DWG # 05-08-1610)



RELATED PARTS

PART NUMBER	DESCRIPTION	COMMENTS
LT1357	High Speed Operational Amplifier	50MHz Gain Bandwidth, 800V/ μ s Slew Rate, I _S = 5mA Max
LT1360	High Speed Operational Amplifier	25MHz Gain Bandwidth, 600V/ μ s Slew Rate, I _S = 2.5mA Max